

Features

- 1200V Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching

V_{RRM}	=	1200 V
$I_F (T_C=158\text{ }^{\circ}\text{C})$	=	40 A
$V_F (T_J\text{ } 25^{\circ}\text{C})$	=	1.35V

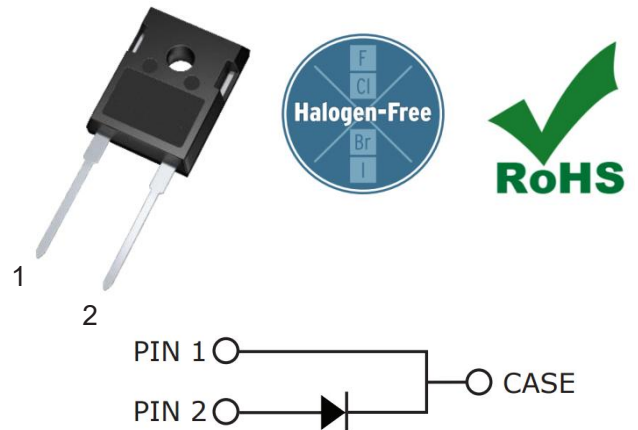
Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies (SMPS)
- Power Factor Correction
- Motor Drives

Package



Maximum Ratings (at $T_C = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	1200	V
Surge Peak Reverse Voltage	V_{RSM}	1200	V
DC Peak Reverse Voltage	V_R	1200	V
Continuous Forward Current $T_C = 25^{\circ}\text{C}$ $T_C = 135^{\circ}\text{C}$ $T_C = 158^{\circ}\text{C}$	I_F	130 67 40	A
Repetitive Peak Forward Surge Current $T_C = 25^{\circ}\text{C}, t_p=10\text{ms}$, Half Sine Pulse $T_C = 110^{\circ}\text{C}, t_p=10\text{ms}$, Half Sine Pulse	I_{FRM}	180 130	A
Non-Repetitive Forward Surge Current $T_C = 25^{\circ}\text{C}, t_p=10\text{ms}$, Half Sine Pulse $T_C = 110^{\circ}\text{C}, t_p=10\text{ms}$, Half Sine Pulse	I_{FSM}	440 360	A
i^2dt value $T_C = 25^{\circ}\text{C}, t_p=10\text{ms}$, Half Sine Pulse $T_C = 110^{\circ}\text{C}, t_p=10\text{ms}$, Half Sine Pulse	$\int i^2 dt$	968 648	A^2s
Power dissipation $T_C = 25^{\circ}\text{C}$ $T_C = 110^{\circ}\text{C}$	P_{tot}	600 260	W
Operating junction Range	T_J	-55 to +175	$^{\circ}\text{C}$
Storage temperature Range	T_{stg}	-55 to +150	$^{\circ}\text{C}$

Thermal Resistance

Parameter	Symbol	Typ.	Unit
Thermal resistance, junction – case.	R_{thJC}	0.25	$^{\circ}\text{C/W}$

Electrical Characteristic (at T_c = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Forward Voltage	V _F	-	1.35	1.7	V	I _F =40A T _j =25°C T _j =175°C
Reverse Current	I _R	-	5	50	μA	V _R =1200V T _j =25°C T _j =175°C
Total Capacitive Charge	Q _C	-	190	-	nC	V _R =800V, T _j =25°C $Q_C = \int_0^{V_R} C(V) dV$
Total Capacitance	C	-	2694	-	pF	T _j =25°C, f=1MHz V _R =0V V _R =400V V _R =800V

Characteristics Curve:

Fig 1: Forward Characteristics

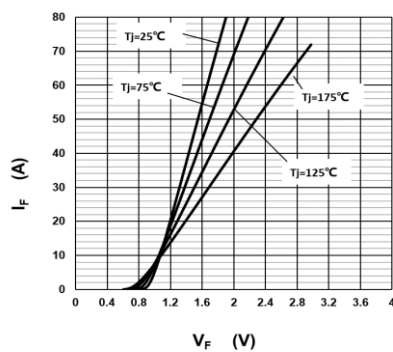


Fig 2: Reverse Characteristics

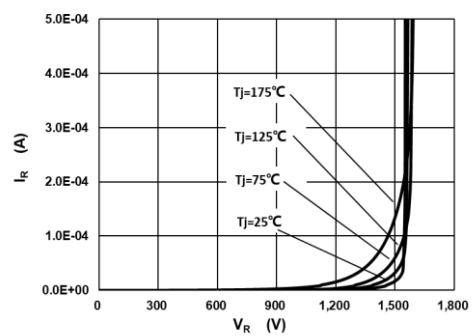


Fig 3: Current Derating

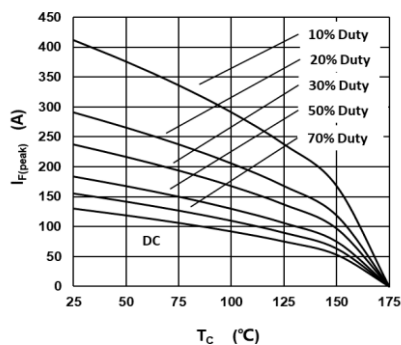


Fig 4: Power Derating

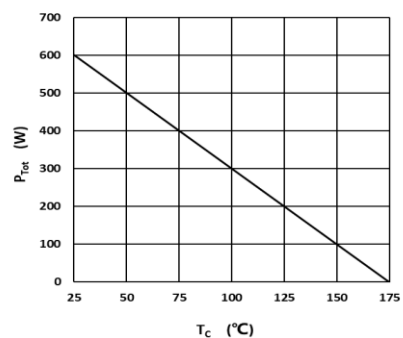


Fig 5: Capacitance vs. Reverse Voltage

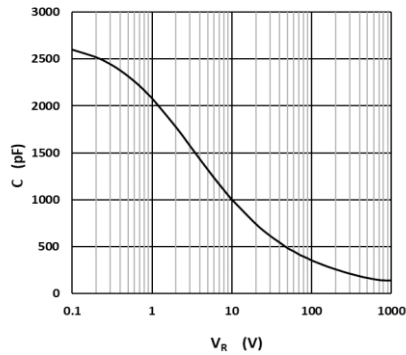


Fig 6: Reverse Charge vs. Reverse Voltage

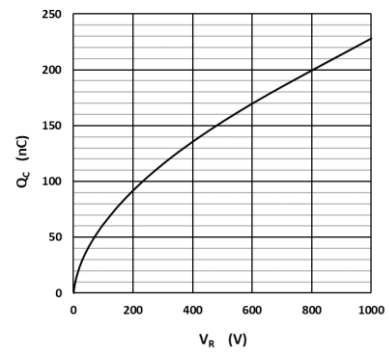


Fig 7: Typical Capacitance Stored Energy

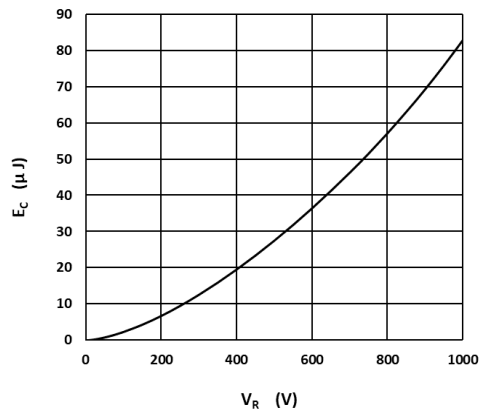
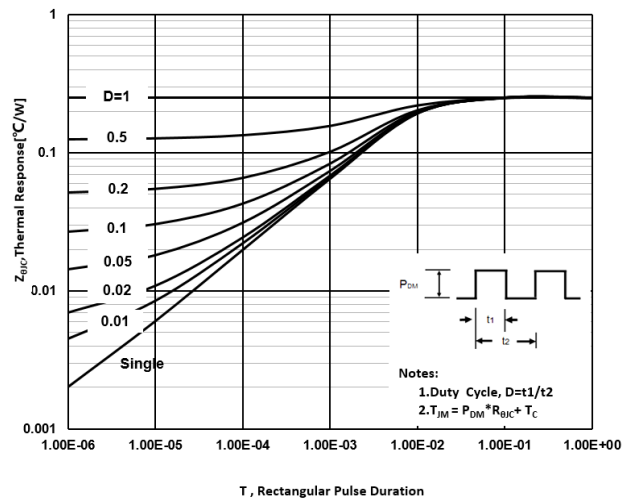
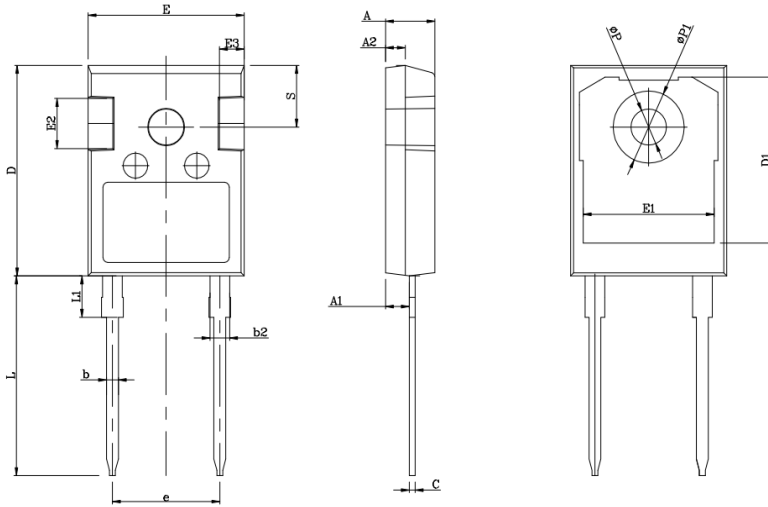


Fig 8: Transient Thermal Impedance



Mechanical Dimensions:



SYMBOL	mm		
	Min	Nom	Max
A	4.80	5.00	5.20
A1	2.23	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.26	13.56
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	10.88BSC		
L	19.82	19.92	20.22
L1	3.94	4.12	4.30
ØP	3.66	3.68	3.75
ØP1	7.08	7.19	7.30
S	6.15BSC		